

Vishay Semiconductors

RoHS

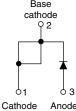
COMPLIANT

HALOGEN

FREE

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A





TO-220AC

PRODUCT SUMMARY							
Package	TO-220AC						
I _{F(AV)}	8 A						
V _R	1200 V						
V _F at I _F	2.4 V						
t _{rr} typ.	28 ns						
T _J max.	150 °C						
Diode variation	Single die						

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRBM) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and mumany other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	8						
Single pulse forward current	I _{FSM}		130	А					
Maximum repetitive forward current	I _{FRM}		32						
Maximum neuror discipation	D_	T _C = 25 °C	73.5	W					
Maximum power dissipation	PD	T _C = 100 °C	29	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C					

Revision: 10-Jul-15

Document Number: 94045

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ELECTRIACL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-					
Maximum forward voltage	V _{FM}	I _F = 8.0 A	-	2.6	3.3	v				
		I _F = 16 A	- 3.4		4.3					
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1					
Maximum reverse		$V_R = V_R$ rated	-	0.31	10					
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	135	1000	μA				
Junction capacitance	CT	V _R = 200 V	-	11	20	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	I _F = 1.0 A, dI _F /dt = 200	A/µs, V _R = 30 V	-	28	-	ns		
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95			
	t _{rr2}	T _J = 125 °C		-	106	160			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	- A nC - Α/μs		
	I _{RRM2}	T _J = 125 °C	l _F = 8.0 A dl _F /dt = 200 A/µs	-	6.2	11			
Povorso rocovoru chargo	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	140	380			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	335	880			
Peak rate of recovery current during $t_{\rm b}$	dl _{(rec)M} /dt1	T _J = 25 °C		-	133	-			
	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-					
Weight			-	6.0	-	g				
vveignt			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC	HFA08TB120							

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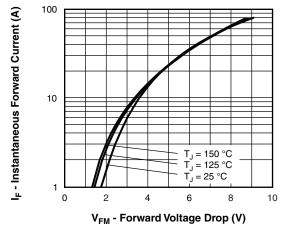


Fig. 1 - Maximum Forward Voltage Drop Characteristics

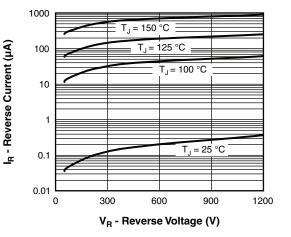


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

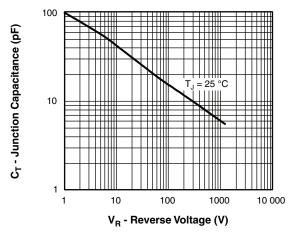
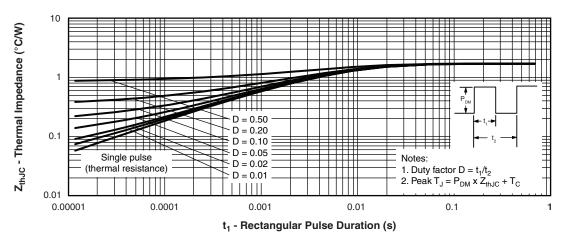


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage







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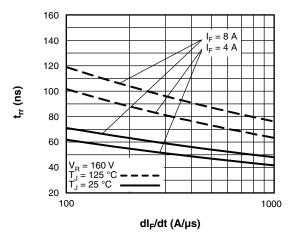


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

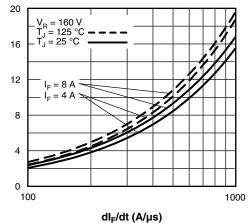


Fig. 6 - Typical Recovery Current vs. dl_F/dt

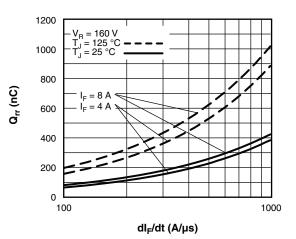


Fig. 7 - Typical Stored Charge vs. dl_F/dt

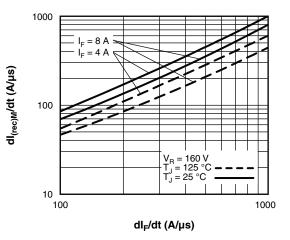


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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I_{rr} (A)



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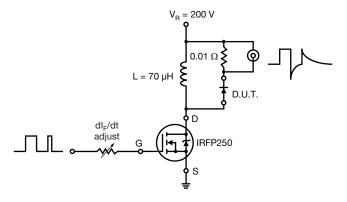


Fig. 9 - Reverse Recovery Parameter Test Circuit

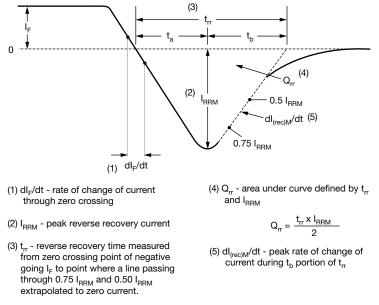
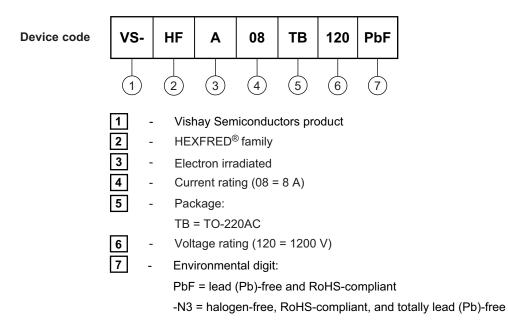


Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA08TB120PbF	50	1000	Antistatic plastic tube						
VS-HFA08TB120-N3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95221						
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224						
	TO-220AC-N3	www.vishay.com/doc?95068						



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TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIMETERS INCHES NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES				
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183		E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055		E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115		е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040		e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4	H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068		L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4	L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024		L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4	L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3	ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355		Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6	θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6						

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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